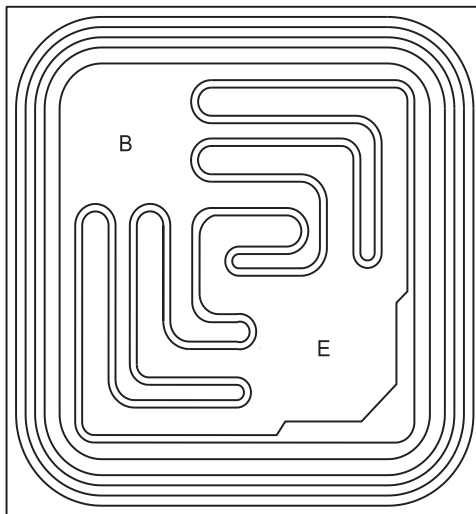


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	19.8 x 19.8 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	4.3 x 4.3 MILS
Emitter Bonding Pad Area	4.3 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE COLLECTOR

**GROSS DIE PER 4 INCH WAFER**

28,960

**PRINCIPAL DEVICE TYPES**

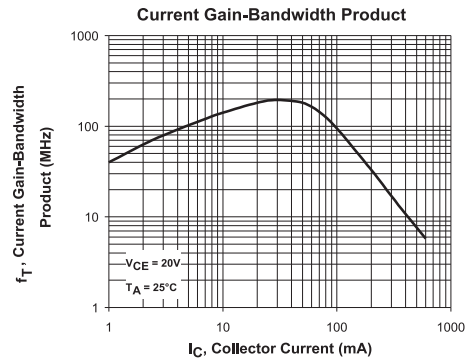
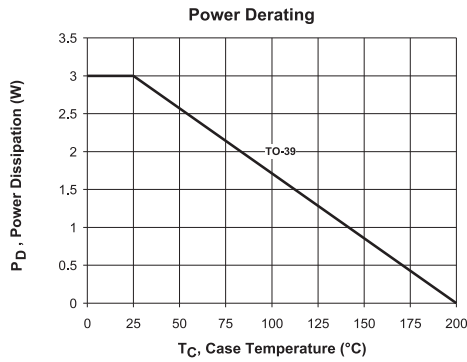
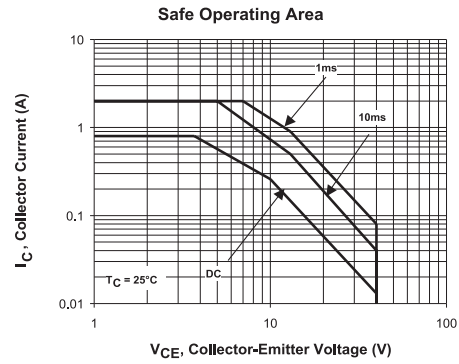
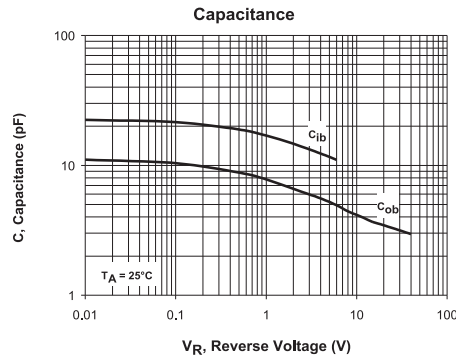
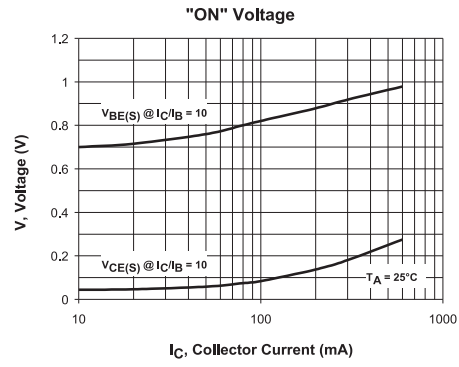
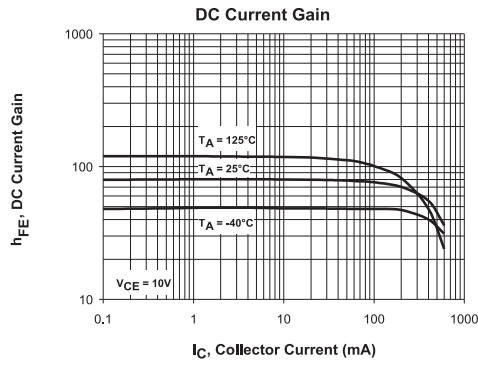
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